

2SD1732

Silicon PNP Triple-Diffused Planar Type

Horizontal Deflection Output

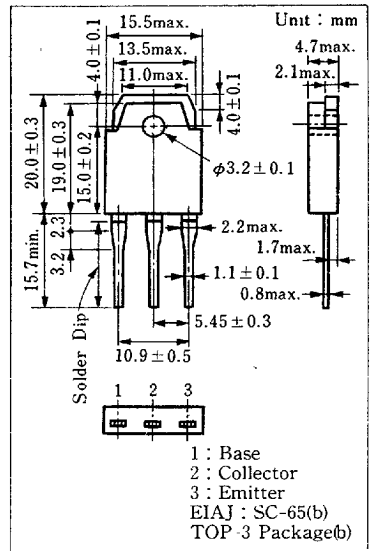
Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)

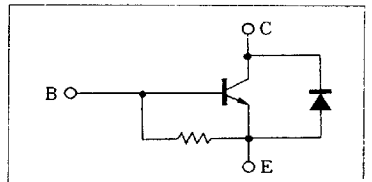
Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CEs}	1500	V
	V _{CeL}	700	V
Emitter-base voltage	V _{EB0}	7	V
Peak collector current	I _{CP}	20	A
Collector current	I _C	7	A
Base current	I _B	3	A
Collector power dissipation	T _c =25°C	100	W
	T _a =25°C	2.5	
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

Package Dimensions



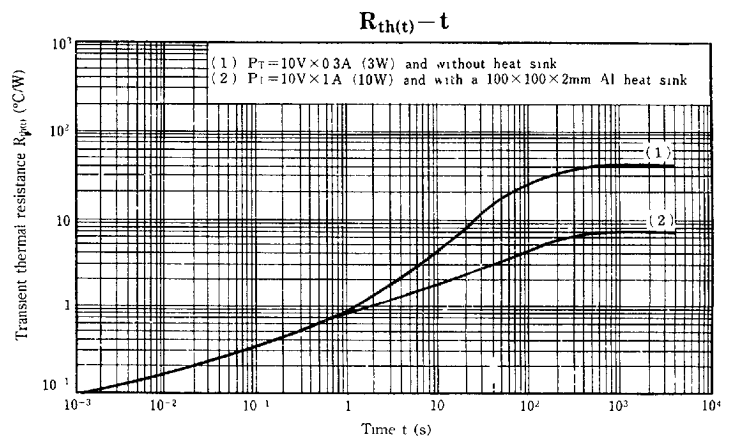
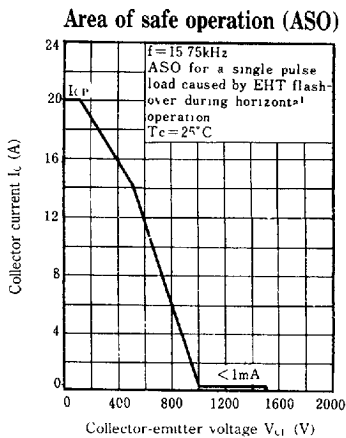
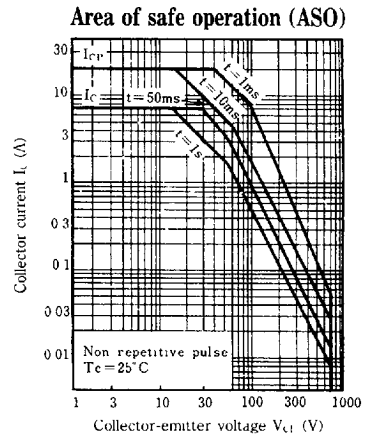
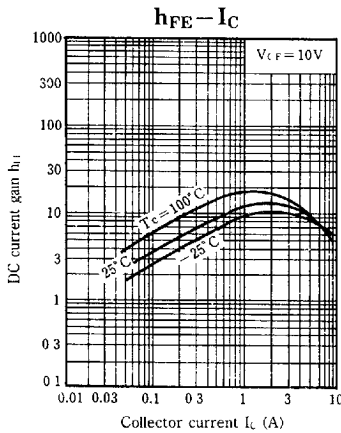
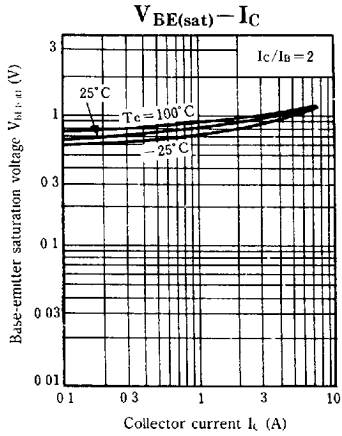
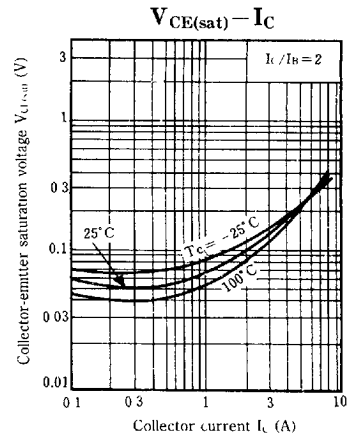
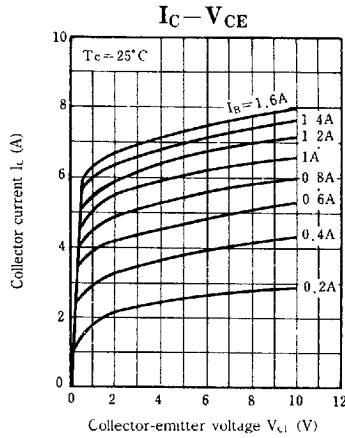
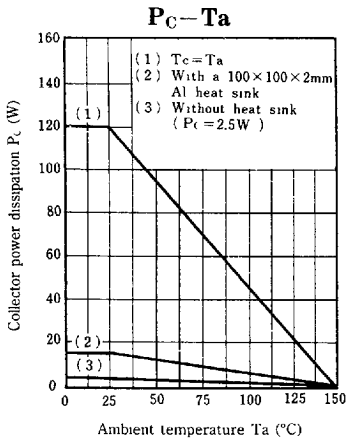
Inner Circuit



Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} =750 V, I _F =0			10	μA
		V _{CB} =1500 V, I _F =0			1	mA
Emitter-base voltage	V _{FBO}	I _E =500 mA, I _C =0	7			V
DC current gain	h _{FE}	V _{CE} =5 V, I _C =1 A	5		25	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =6 A, I _B =1.4 A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =6 A, I _B =1.4 A			1.5	V
Transition frequency	f _T	V _{CE} =10V, I _C =1A, f=0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C =6A, I _{B1} =1.4A			11	μs
Fall time (L load)	t _f	I _{B2} =-1.4A, L _{leak} =5μH			0.8	μs
Storage time (R load)	t _{stg}	I _C =6 V, I _{B1} =1.2 A		1.5		μs
Fall time (R load)	t _f	I _{B2} =-2.4 A, V _{CC} =200 V		0.2		μs
Diode forward voltage	V _F	I _C =-7 A, I _B =0			-2.3	V

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